

CLAIMS

1. A semiconductor device, comprising:

- a semiconductor substrate;
- a first insulating film formed on said semiconductor substrate;
- a polysilicon resistor film formed on said first insulating film;
- a second insulating film formed on said resistor film;
- a high heat conductor film consisting of a highly heat-conducting material formed on said second insulating film; and
- a pair of terminal wirings formed on said second insulating film and connected to said resistor film, wherein a thickness of said second insulating film is thinner than a thickness of said resistor film.

2. A semiconductor device, comprising:

- a semiconductor substrate;
- a first insulating film formed on said semiconductor substrate;
- a polysilicon resistor film formed on said first insulating film;
- a second insulating film formed on said resistor film;

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a high heat conductor film consisting of a highly heat-conducting material formed on said second insulating film; and

a pair of terminal wirings formed on said second insulating film and connected to said resistor film,

wherein a thickness of said high heat conductor film is thicker than a thickness of said resistor film.

3. The semiconductor device according to claim 2, wherein the thickness of said high heat conductor film is twice the thickness of said resistor film or thicker.

4. The semiconductor device according to claim 2, wherein a width of said high heat conductor film is wider than a width of said resistor film.

5. The semiconductor device according to claim 2, wherein said high heat conductor film is united with one of said terminal wirings.